Karim S Karim

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/1961734/publications.pdf

Version: 2024-02-01

	516710	454955
959	16	30 g-index
citations	h-index	g-index
50	F.0	1017
59	59	1017
docs citations	times ranked	citing authors
	citations 59	959 16 citations h-index 59 59

#	Article	IF	Citations
1	Improving adhesion quality of SU-8 to gold thin film for absorption grating fabrication in x-ray phase-contrast imaging. , 2022, , .		O
2	A novel multi-layer grating structure for x-ray phase-contrast imaging. , 2022, , .		0
3	A Monolithic Amorphous-Selenium/CMOS Visible-Light Imager With Sub-9-ξm Pixel Pitch and Extended Full-Well Capacity. IEEE Sensors Journal, 2021, 21, 339-346.	4.7	O
4	A Monolithic Amorphous-Selenium/CMOS Single-Photon-Counting X-Ray Detector. IEEE Transactions on Electron Devices, 2021, 68, 1746-1752.	3.0	3
5	High-energy micrometre-scale pixel direct conversion X-ray detector. Journal of Synchrotron Radiation, 2021, 28, 1081-1089.	2.4	11
6	Recent Progress in the Development of a-Se/CMOS Sensors for X-ray Detection. Quantum Beam Science, 2021, 5, 29.	1.2	7
7	Use of Pulse-Height Spectroscopy to Characterize the Hole Conduction Mechanism of a Polyimide Blocking Layer Used in Amorphous-Selenium Radiation Detectors. IEEE Transactions on Electron Devices, 2020, 67, 633-639.	3.0	9
8	Pâ€130: A Full Screen Biometric Identification Approach for OLED Displays by Using Nearâ€Infrared OLED. Digest of Technical Papers SID International Symposium, 2020, 51, 1855-1858.	0.3	1
9	Performance of amorphous selenium based unipolar charge sensing detector for photon-counting X-ray imaging. , 2020, , .		2
10	LTPS Active Pixel Circuit With Threshold Voltage Compensation for X-Ray Imaging Applications. IEEE Transactions on Electron Devices, 2019, 66, 4216-4220.	3.0	12
11	Nanocrystalline Silicon Lateral MSM Photodetector for Infrared Sensing Applications. IEEE Transactions on Electron Devices, 2018, 65, 584-590.	3.0	9
12	Extending the geopolitical supply risk method: material "substitutability―indicators applied to electric vehicles and dental X-ray equipment. International Journal of Life Cycle Assessment, 2018, 23, 2024-2042.	4.7	32
13	Wireless <italic>LC</italic> -Type Passive Humidity Sensor Using Large-Area RF Magnetron Sputtered ZnO Films. IEEE Transactions on Electron Devices, 2018, 65, 3447-3453.	3.0	12
14	Lateral Organic Semiconductor Photodetector: Effect of Electrode Spacing. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-7.	2.9	3
15	Technical Note: Detective quantum efficiency simulation of aâ€ S e imaging detectors using ARTEMIS. Medical Physics, 2017, 44, 4035-4039.	3.0	O
16	a-Si:H TFT-Silicon Hybrid Low-Energy X-Ray Detector. IEEE Transactions on Electron Devices, 2017, 64, 1624-1629.	3.0	4
17	MTF and DQE enhancement using an apodizedâ€aperture xâ€ray detector design. Medical Physics, 2017, 44, 4525-4535.	3.0	3
18	X-Ray Dosimetry During Low-Intensity Femtosecond Laser Ablation of Molybdenum in Ambient Conditions. IEEE Transactions on Nuclear Science, 2017, 64, 2519-2522.	2.0	3

#	Article	IF	CITATIONS
19	Theoretical and Monte Carlo optimization of a stacked three-layer flat-panel x-ray imager for applications in multi-spectral diagnostic medical imaging. Proceedings of SPIE, 2016, 9783, .	0.8	4
20	Characterization of Lag Signal in Amorphous Selenium Detectors. IEEE Transactions on Electron Devices, 2016, 63, 704-709.	3.0	3
21	Model-Based Initial Bias (MIB): Toward a Single-Iteration Optical Proximity Correction. IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems, 2016, 35, 1630-1639.	2.7	2
22	Direct-Conversion CMOS X-Ray Imager With <inline-formula> <tex-math notation="LaTeX">\$5.6 ~mu ext{m} imes 6.25~mu ext{m}\$ </tex-math></inline-formula> Pixels. IEEE Electron Device Letters, 2015, 36, 481-483.	3.9	34
23	Characterization of Optically Sensitive Amorphous Selenium Photodetector at High Electric Fields. IEEE Transactions on Electron Devices, 2015, 62, 2364-2366.	3.0	4
24	Reactive Ion-Assisted Deposition of Cerium Oxide Hole-Blocking Contact for Leakage-Current Suppression in an Amorphous Selenium Multilayer Structure. IEEE Sensors Journal, 2015, 15, 3871-3876.	4.7	4
25	System design of a low-cost digital x-ray detector. , 2014, , .		1
26	UV Organic Semiconductor Photoconductor with Low Dark Current at High Electric Field. Materials Research Society Symposia Proceedings, 2014, 1698, 53.	0.1	1
27	Low Dark Current Amorphous Silicon Metal-Semiconductor-Metal Photodetector for Digital Imaging Applications. IEEE Electron Device Letters, 2014, 35, 235-237.	3.9	27
28	Lateral Organic Semiconductor Photodetector. Part I: Use of an Insulating Layer for Low Dark Current. IEEE Transactions on Electron Devices, 2014, 61, 3465-3471.	3.0	7
29	Enhanced Dark Current Suppression of Amorphous Selenium Detector With Use of IGZO Hole Blocking Layer. IEEE Transactions on Electron Devices, 2014, 61, 3355-3357.	3.0	15
30	Measurement of UV from a Microplasma by a Microfabricated Amorphous Selenium Detector. IEEE Transactions on Electron Devices, 2013, 60, 880-883.	3.0	37
31	Effect of burst and recombination models for Monte Carlo transport of interacting carriers in a-Se x-ray detectors on Swank noise. Medical Physics, 2013, 41, 011904.	3.0	4
32	K-Edge Imaging Using Dual-Layer and Single-Layer Large Area Flat Panel Imagers. IEEE Transactions on Nuclear Science, 2012, 59, 1856-1861.	2.0	7
33	Study of the transient response of PI/a-Se photodetectors for indirect conversion medical imaging. , 2012, , .		2
34	Photon-Quantum-Noise-Limited Pixel Architecture in Amorphous-Silicon Technology for Large-Area Digital Imaging Applications. IEEE Transactions on Electron Devices, 2012, 59, 3017-3023.	3.0	0
35	Investigation of Hole-Blocking Contacts for High-Conversion-Gain Amorphous Selenium Detectors for X-Ray Imaging. IEEE Transactions on Electron Devices, 2012, 59, 2403-2409.	3.0	47
36	Amorphous-Selenium-Based Three-Terminal X-Ray Detector With a Gate. IEEE Electron Device Letters, 2011, 32, 782-784.	3.9	8

#	Article	IF	CITATIONS
37	Low Dark-Current Lateral Amorphous-Selenium Metal–Semiconductor–Metal Photodetector. IEEE Electron Device Letters, 2011, 32, 1263-1265.	3.9	21
38	Direct-Conversion X-Ray Detector Using Lateral Amorphous Selenium Structure. IEEE Sensors Journal, 2011, 11, 505-509.	4.7	17
39	Selenium coated CMOS passive pixel array for medical imaging. Proceedings of SPIE, 2011, , .	0.8	1
40	Amorphous and Polycrystalline Photoconductors for Direct Conversion Flat Panel X-Ray Image Sensors. Sensors, 2011, 11, 5112-5157.	3.8	372
41	Spatiotemporal Monte Carlo transport methods in x-ray semiconductor detectors: Application to pulse-height spectroscopy in a-Se. Medical Physics, 2011, 39, 308-319.	3.0	19
42	Recombination models for spatio-temporal Monte Carlo transport of interacting carriers in semiconductors. Applied Physics Letters, 2011, 98, 242111.	3.3	7
43	10.1063/1.3599602.1.,2011,,.		1
44	Fast Lateral Amorphous-Selenium Metal–Semiconductor–Metal Photodetector With High Blue-to-Ultraviolet Responsivity. IEEE Transactions on Electron Devices, 2010, 57, 1953-1958.	3.0	19
45	An a-Si Active Pixel Sensor (APS) Array for Medical X-ray Imaging. IEEE Transactions on Electron Devices, 2010, 57, 3020-3026.	3.0	24
46	Digital X-Ray Imaging Using Avalanche a-Se Photoconductor. IEEE Sensors Journal, 2010, 10, 347-352.	4.7	19
47	Silicon X-Ray Detector With Integrated Thin-Film Transistor for Biomedical Applications. IEEE Electron Device Letters, 2010, 31, 147-149.	3.9	6
48	Lateral metal-semiconductor-metal photodetectors based on amorphous selenium. Applied Physics Letters, 2009, 95, 013505.	3.3	35
49	X-Ray Detection Using a Two-Transistor Active Pixel Sensor Array Coupled to an a-Se X-Ray Photoconductor. IEEE Sensors Journal, 2009, 9, 51-56.	4.7	6
50	Structural and electrical characteristics of nanocrystalline silicon prepared by hot-wire chemical vapor deposition on polymer substrates. Thin Solid Films, 2008, 516, 7418-7421.	1.8	1
51	Characterization of Short-Wavelength-Selective a-Si:H MSM Photoconductors for Large-Area Digital-Imaging Applications. IEEE Transactions on Electron Devices, 2008, 55, 337-342.	3.0	17
52	Two-Transistor Active Pixel Sensor Readout Circuits in Amorphous Silicon Technology for High-Resolution Digital Imaging Applications. IEEE Transactions on Electron Devices, 2008, 55, 2121-2128.	3.0	24
53	UV-Enhanced a-Si:H Metal–Semiconductor–Metal Photodetector. IEEE Electron Device Letters, 2008, 29, 1007-1010.	3.9	14
54	Charge-Gated Thin-Film Transistors for High Resolution Digital Imaging Applications. IEEE Electron Device Letters, 2008, 29, 859-862.	3.9	1

#	Article	IF	CITATIONS
55	Design and feasibility of active matrix flat panel detector using avalanche amorphous selenium for protein crystallography. Medical Physics, 2008, 35, 4324-4332.	3.0	17
56	Two-Transistor Active Pixel Sensor for High Resolution Large Area Digital X-ray Imaging., 2007,,.		10
57	Intelligent Pixel Architectures for Digital Medical Imaging Applications. ECS Transactions, 2007, 8, 289-293.	0.5	2
58	Low Temperature a-Si:H Pixel Circuits for Mechanically Flexible AMOLED Displays. Materials Research Society Symposia Proceedings, 2003, 769, 221.	0.1	4
59	Improving Amorphous Selenium Photodetector Performance Using an Organic Semiconductor. Key Engineering Materials, 0, 543, 451-454.	0.4	4